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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

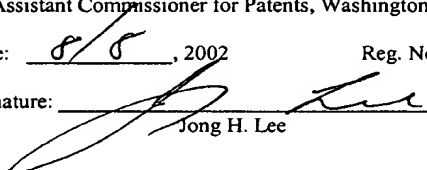
Inventor(s) : Joerg SCHAEFER et al.
Serial No. : 09/238,262
Filed : January 27, 1999
For : METHOD OF PRODUCING STRUCTURED WAFERS
Examiner : Anita Karen Alanko
Art Unit : 1746

Assistant Commissioner for
Patents
Washington, D.C. 20231

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AMENDMENT

SIR:

In response to the Office Action dated April 10, 2002, kindly amend the above-identified application before examination, as set forth below.

IN THE SPECIFICATION:

please replace the paragraph beginning on page 2, line 7, with the following paragraph:

Figure 1 shows a first embodiment of the method according to the present invention as a two-sided one-step etching process. Part 1 shows a cross-sectional view of wafer 20, which made be made of a single material, with a front side 22, a back side 23 and an edge area 21. The wafer is shown only partially, continuing toward the left, where it is delimited by another edge area (not shown). A nitride layer is applied to the wafer by gas phase deposition. Then the nitride layer is structured by a conventional photoresist technique, with the resist being applied to the nitride layer, exposed selectively and then developed; (when using a positive resist) the exposed part of the resist is next removed, then the exposed part of the